

## IGBT MODULE ( N series )

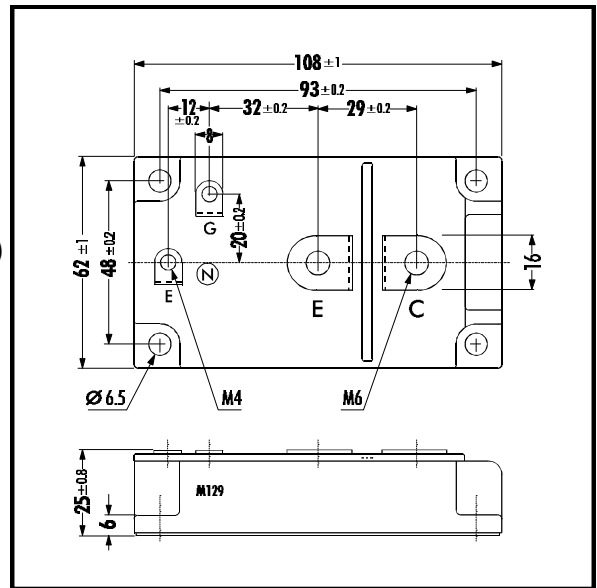
### ■ Features

- Square RBSOA
- Low Saturation Voltage
- Less Total Power Dissipation
- Improved FWD Characteristic
- Minimized Internal Stray Inductance
- Overcurrent Limiting Function (~3 Times Rated Current)

### ■ Applications

- High Power Switching
- A.C. Motor Controls
- D.C. Motor Controls
- Uninterruptible Power Supply

### ■ Outline Drawing



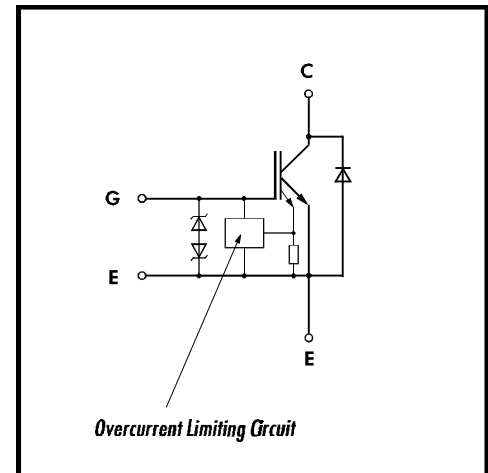
### ■ Maximum Ratings and Characteristics

#### • Absolute Maximum Ratings ( T<sub>c</sub>=25°C )

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V <sub>CEs</sub>	600	V
Gate -Emitter Voltage	V <sub>GES</sub>	± 20	V
Collector Current	Continuous	I <sub>C</sub>	600
	1ms	I <sub>C PULSE</sub>	1200
	Continuous	-I <sub>C</sub>	600
	1ms	-I <sub>C PULSE</sub>	1200
Max. Power Dissipation	P <sub>C</sub>	2000	W
Operating Temperature	T <sub>i</sub>	+150	°C
Storage Temperature	T <sub>stg</sub>	-40 ~ +125	°C
Isolation Voltage	V <sub>is</sub>	2500	V
Screw Torque	Mounting *1	3.5	Nm
	Terminals *2	4.5	
	Terminals *3	1.7	

Note: \*1:Recommendable Value; 2.5 - 3.5 Nm (M5) or (M6)  
 \*2:Recommendable Value; 3.5 - 4.5 Nm (M6)  
 \*3:Recommendable Value; 1.3 - 1.7 Nm (M4)

### ■ Equivalent Circuit



#### • Electrical Characteristics ( at T<sub>f</sub>=25°C )

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I <sub>CEs</sub>	V <sub>GE</sub> =0V V <sub>CE</sub> =600V			4.0	mA
Gate-Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V V <sub>GE</sub> =± 20V			60	μA
Gate-Emitter Threshold Voltage	V <sub>GE(th)</sub>	V <sub>GE</sub> =20V I <sub>C</sub> =600mA	4.5		7.5	V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	V <sub>GE</sub> =15V I <sub>C</sub> =600A			2.8	V
Input capacitance	C <sub>ies</sub>	V <sub>GE</sub> =0V		39600		pF
Output capacitance	C <sub>oes</sub>	V <sub>CE</sub> =10V		8800		
Reverse Transfer capacitance	C <sub>res</sub>	f=1MHz		4000		
Turn-on Time	t <sub>ON</sub>	V <sub>CC</sub> =300V		0.6	1.2	μs
	t <sub>r</sub>	I <sub>C</sub> =600A		0.2	0.6	
Turn-off Time	t <sub>OFF</sub>	V <sub>GE</sub> =± 15V		0.6	1.0	
	t <sub>f</sub>	R <sub>G</sub> =2.7Ω		0.2	0.35	
Diode Forward On-Voltage	V <sub>F</sub>	I <sub>F</sub> =600A V <sub>GE</sub> =0V			3.0	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =600A			300	ns

#### • Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	R <sub>th(f-c)</sub>	IGBT			0.063	°C/W
	R <sub>th(f-e)</sub>	Diode			0.11	
	R <sub>th(c-f)</sub>	With Thermal Compound		0.0125		